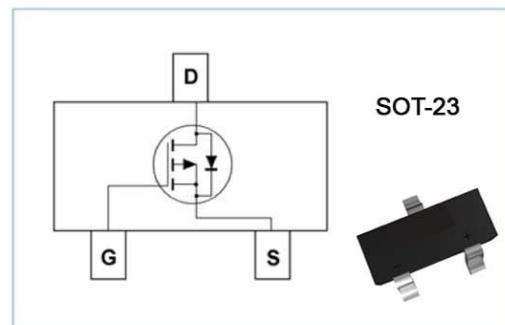


•Feature

-16V/-3A, R_{D(S)}(ON) = 160m Ω (MAX) @V_{GS} = -4.5V.
 R_{D(S)}(ON) = 240m Ω (MAX) @V_{GS} = -2.5V.

Super High dense cell design for extremely low R_{D(S)}(ON)
 Reliable and Rugged
 SOT-23 for Surface Mount Package


•Applications

Power Management
 Portable Equipment and Battery Powered Systems.

•Absolute Maximum Ratings

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	-16	V
Gate-Source Voltage	V _{GS}	±8	V
Drain Current-Continuous	I _D	-3	A

•Electrical Characteristics

T_A=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	V _{GS} =0V, I _D =-250μA	-16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V	-	-	-5	μA
Gate Body Leakage Current, Forward	IGSSF	V _{GS} =8V, V _{DS} =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V _{GS} =-8V, V _{DS} =0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =-250μA	-0.45	-	-1.5	V
Static Drain-source	R _{D(S)} (ON)	V _{GS} =-4.5V, I _D =-3.0A	-	-	160	mΩ
On-Resistance		V _{GS} =-2.5V, I _D =-2.0A	-	-	240	mΩ
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1.25A			-1.8	V

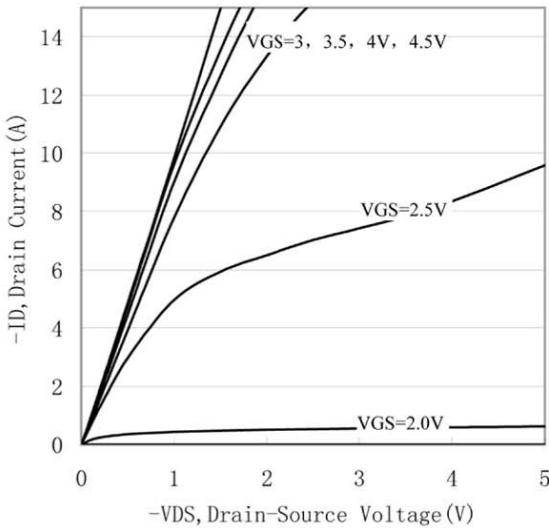


Figure 1. Output Characteristics

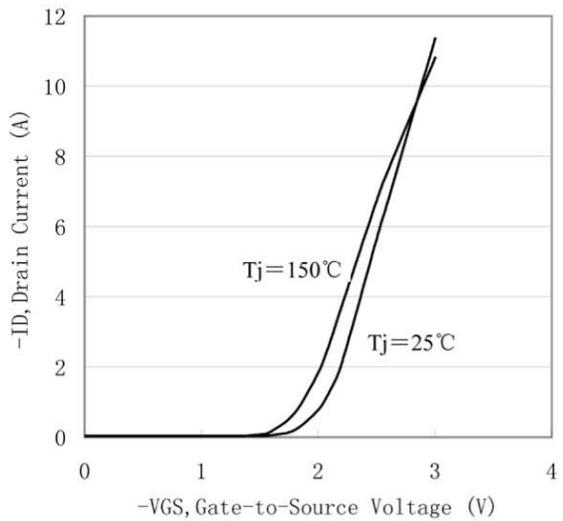


Figure 2. Transfer Characteristics

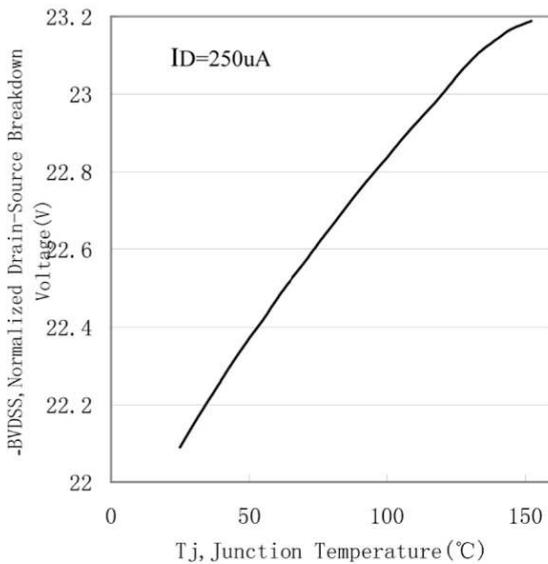


Figure 3. Breakdown Voltage Variation with Temperature

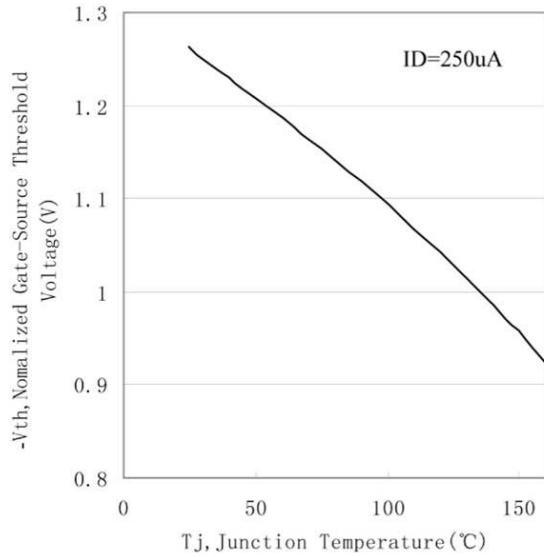


Figure 4. Gate Threshold Variation with Temperature

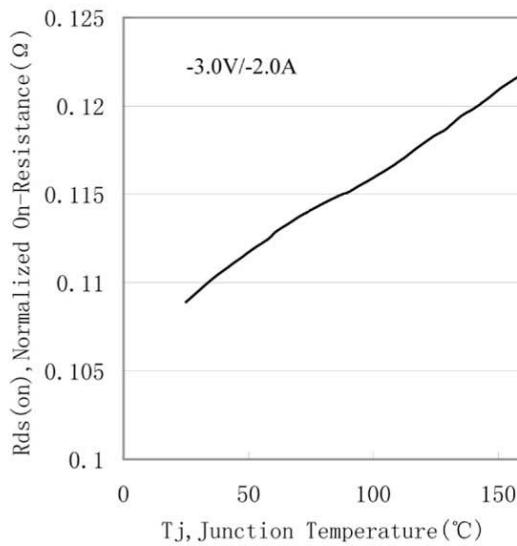


Figure 5. On-Resistance Variation with Temperature

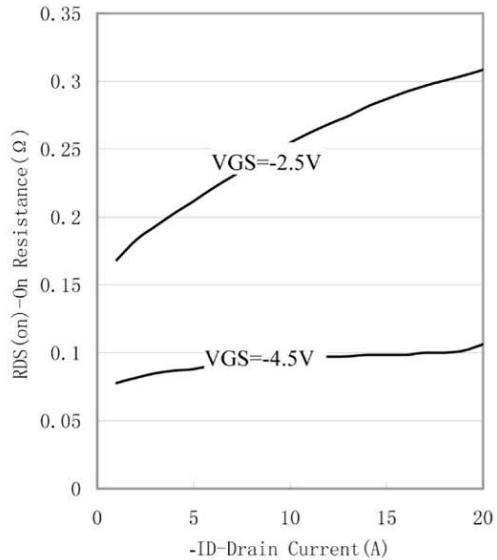


Figure 6. On-Resistance vs. Drain Current

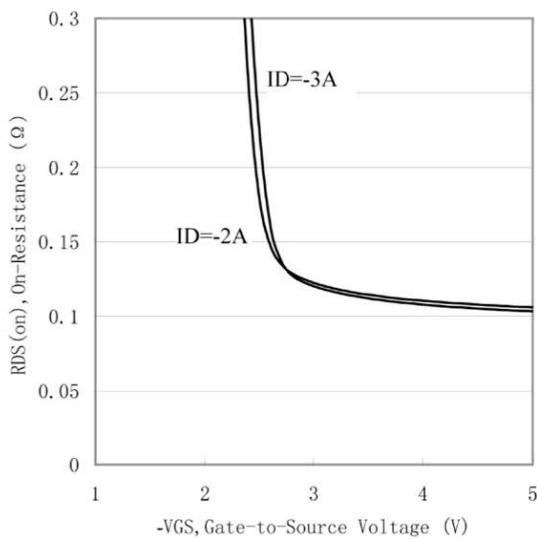


Figure 7. On-Resistance vs. Gate-to-Source Voltage

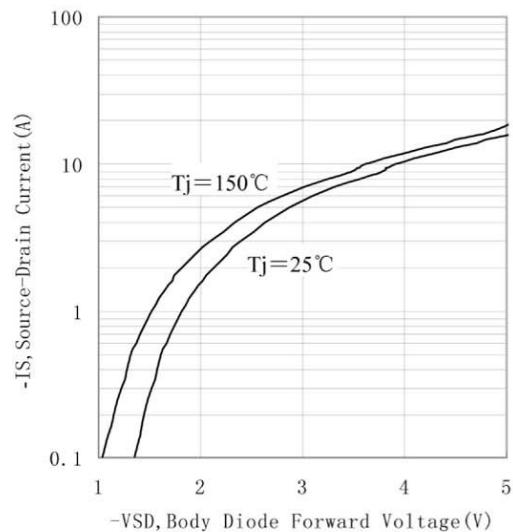


Figure 8. Source-Drain Diode Forward Voltage

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)